



Issue date:

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**Notification of Product/Process Change**  
**Doc. No.: 3026002**

This letter intends as a formal notification of change to products which are currently supplied by ROHM Co., Ltd.

ROHM Co., Ltd. requires customers to provide acknowledgment of the receipt of this notification within 30 days from the date of this notice. Lack of acknowledgment of this notice within 30 days is considered as acceptance of the change.

After acknowledgement of the customer, lack of additional response within 90 day period constitutes acceptance of the change according to JEDEC Standard J-STD-046.

Your understanding and cooperation would be highly appreciated.

Issue Date: March 1, 2026

Title of change	Change of wafer manufacturing site from ROHM HQ Plant to Shiga Plant (Si power transistors)		
Affected product(s)	Manufacturer part number	Customer part number	
	Refer attached sheet		
Detailed description of change	Before	After	
	Front-end fabrication plant; Kyoto	Front-end fabrication plant; Shiga	
Reason for change	As part of the consolidation of production lines, the front-end operations will be centralized at the Shiga plant.		
Anticipated impact on quality	The implemented change does not affect product quality.		
Identification of change	Identification can be achieved through marking-based traceability.		
Planned first ship date	April 1, 2027	Sample available schedule :	Mar,1,2026
Comments	If you need existing products, please place your orders for the required quantities by March 31, 2027. Following the consolidated production, we would appreciate your cooperation in receiving the products in a single shipment.		
Supplier contact	Please contact the local ROHM sales office or the authorized distributor.		
Notes			



Electronics for the Future

# **Notification No. 3026002**

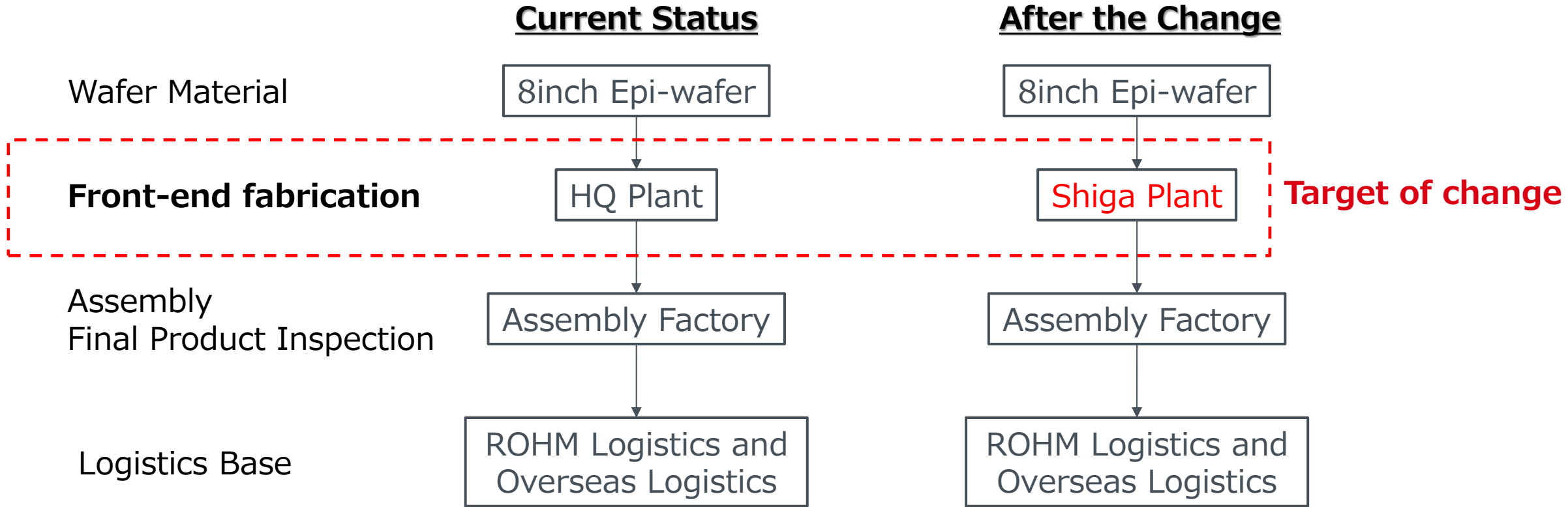
## **Change of wafer manufacturing site from ROHM HQ Plant to Shiga Plant (Si power transistors)**

March 2026  
ROHM Co., Ltd  
LV Device Division

# 3026002-1. Overview of Change Application



<b>Notification No.</b>	<b>3026002</b>
<b>Subject</b>	<b>Change of wafer manufacturing site from ROHM HQ Plant to Shiga Plant (Si power transistors)</b>
<b>Background</b>	<b>Due to the consolidation and streamlining of manufacturing lines aimed at improving production efficiency in the front-end fabrication plant, the production of LV-MOSFETs currently manufactured at HQ Plant will be transferred to Shiga Plant.</b>
<b>Details of Change</b>	<b>Change of Production Plant (Headquarters → Shiga Plant)</b>
<b>Target Products</b>	<b>Si power: 16 models</b> <b>(Please refer to the change request form for the relevant part numbers of your company.)</b>
<b>Requested Response Date</b>	<b>March 31, 2027</b>
<b>Planned first ship date</b>	<b>April 1, 2027</b>
<b>Last time buy</b>	<b>March 31, 2027</b>
<b>Last time shipment</b>	<b>March 31, 2028</b>



The front-end fabrication will be transferred from HQ Plant to Shiga Plant. There are no changes to wafer materials or processes after the back-end process (package assembly process).

# 3026002-3. ROHM Shiga Plant Data



- Company name      ROHM Co.,Ltd Shiga Plant
- Location              2-8-1, Seiran, Otsu-shi, Shiga
- Date established      April 20, 2015
- Products              MOSFET, IGBT, Diode, IPD, RASMID \*1

\* 1 ROHM Advanced Smart Micro Device: the ultra-small devices with ROHM's original technology.

April. 2015	ROHM Shiga established
August. 2016	Started mass production of MOSFETs
November. 2016	Started mass production of RASMIDs
August. 2017	ISO9001 (2015) certified
November. 2017	ISO14001 (2015) certified
December. 2017	Started mass production of diodes
August. 2018	IATF16949 (2016) certification planned
August. 2018	OHSAS18001 certification planned
April. 2020	Merged into ROHM Co., Ltd. and became ROHM Co., Ltd. Shiga Plant

# 3026002-3. HQ Plant / Shiga Plant Factory Comparison

		Before the Change	After the Change
Production Plant		HQ Plant	Shiga Plant
Wafer Diameter		8inch	8inch
Cleanroom	Temperature	23°C	23°C
	Humidity	45%	45%
	Cleanliness (Wafer Exposure Area)	Class3(0.1μm)	Class3(0.1μm)
	Airflow System	Laminar Flow	Laminar Flow
Minimum Design Rule		0.15μm	0.15μm

The cleanroom environment at Shiga Plant is equivalent to that of HQ Plant, and there are no issues with the production environment.

# 3026002-4. Summary of 4M Change Points

		Before Change	After Change	Comments on Change Points
Environment		HQ Plant	Shiga Plant	Change already implemented for other models
Man	-	Licensed operators	Licensed operators	Licensed operators at each plant
Machine	•Equipment	Existing equipment	Equivalent equipment	No issues confirmed after characteristic check
	•Process control	According to QC process chart	Managed with equivalent content	No difference
	•Management method	SPC management	Equivalent functions available	No difference
Material	•Wafer	8inch	Same material	No difference
	•Reticle size	6inch	Same design	No issues confirmed after characteristic check
	•Others	Chemicals, wiring materials, etc.	Equivalent performance materials	No issues confirmed after characteristic check
Method	•Work method	Work standards	Equivalent standards	No differences in work procedures
	•Inspection	According to inspection standards	Equivalent content	No difference
	•Traceability	15 years	Managed with equivalent content	No difference
Measurement	•Measuring equipment	Existing equipment	Equivalent type of equipment	Equipment correlation completed, no issues
	•Management method	According to equipment QC process chart	Equivalent management content	No difference

We have confirmed that there are no issues with any of the items in accordance with the 4M change points.

# 3026002-4. Identification of change

Package	TSMT8M	TSMT6M	TUMT3	HSOP8	HSMT8	HUML6
Part number: •Before change (HQ Plant) •After change (Shiga Plant)	Same part number					
Product marking (Lot No.)						

Identification can be achieved through marking-based traceability.

# 3026002-5. Extraction of Concerns and Confirmation Results

Item	Concern	Before Change (HQ)	After Change (Shiga)	Judgment
Electrical Characteristics	Variation in characteristics	Standard	Equivalent to HQ product	No problem
Yield	Yield decrease	Standard	No decrease compared to HQ product	No problem
Primary Characteristics	Variation in primary characteristics	Standard	Equivalent to HQ product (Refer to the following)	No problem

## <Primary Characteristics\_Process Capability Index Comparison Results> 0.15μm MOSFET Product Quality

No.	Process	Before Change (HQ)	After Change (Shiga)	Judgment
		Cpk	Cpk	
1	Trench Dimension	1.35	1.64	No Issue
2	Trench Depth	1.41	1.43	No Issue
3	Gate Oxide Thickness	2.11	2.51	No Issue
4	Gate Poly-Si Thickness	3.31	4.43	No Issue
5	ILD Thickness	2.45	2.87	No Issue
6	Contact Dimension	1.98	2.16	No Issue
7	Cont Depth	1.35	1.39	No Issue

All concerns have been confirmed to present no issues.

# 3026002-6. Reliability test result

## 1. Test result

Test item	Test conditions	Standard	Test time	n(pcs)	Failure Pn (pcs)
Temperature humidity bias (THB)	Ta=85°C, Rh=85%, Vds-max	JESD22-A101	1,000h	22pcs	0
Temperature cycle (TCY)	-55°C (30min) - +150°C (30min)	JESD22-A104	200cyc	22pcs	0
Pressure cooker (PCT)	Ta=121°C, 15psig, Rh=100%	JESD22-A102	100h	22pcs	0
High temperature reverse bias (HTRB)	Ta=150°C, Vds-max	JESD22-A108	1,000h	22pcs	0
High temperature gate bias (HTGB)	Ta=150°C, Vgs-max	JESD22-A108	1,000h	22pcs	0

## 2. Measurement Item & Criteria

Item	Condition	Criteria
		Electrical characteristic
BVDSS, VGS	Par specification	Must be in the values specified in specification sheet.
IGSS, IDSS, IDGO	Par specification	
Vgs(th), Rds(on), Yfs	Par specification	
Appearance	Visual inspection	No significant change

Reliability test results show no problem.



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Package	Public (External) PN
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No.3026002

TSMT8	QH8K22TCR
HSOP8	RS1G260MNTB
TSMT8	RQ7E110AJTCR
HUML6	RF4E060AJTCR
TUMT3	RAF040P01FMMTCL
TUMT3	RAF040P01FMMTCL
TSMT6	RQ6E050ATFGMTCR
TSMT6	RQ6E050ATFGMTCR
TSMT6	RQ6E030ATFGMTCR
TSMT6	RQ6E030ATFGMTCR
HSMT8	RQ3E100GNTB
HSOP8	RS1E130GNTB
HSOP8	RS1E280GNTB
HSMT8	RQ3E180GNTB
HSMT8	RQ3E150GNTB
HUML6	RF4E110GNTR